

11/08/08



769 08-10102 (2) 17:46:08:7.41

134

Do not enter
JTB/1
02/11/2008

UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Mitsubishi Electric** Class: Art Unit: **2833**
 Application Number: **10772253** Examiner: **Thomas V. Pham**
 Filed: **February 6, 2004** Continuation Number: **6401**

For: **METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE
 INCLUDING A LOW-TEMPERATURE LOWER
 ELECTRODE FORMING STEP**

Attorney/Agent Number: **002868**
 Current Number: **50824**

DECLARATION UNDER 37 C.F.R. § 1.133

Continuation of Patent
 P.O. Box 4420
 Alexandria, VA 22315-1420

Date Filed

Sir:

I, **Mitsuhiko Fujiki**, a citizen of Japan, hereby declare and state the following:

1. I graduated from Osaka University of Osaka, Japan in 1996 with a Ph.D. degree in Science.
2. Since 1997, I have been employed by Fujitsu Limited of Kanagawa, Japan where my present title is **engineer of DRAM development**. During my employment there, I have conducted research and development of processing for **FeRAM**.
3. I am the author of the following publications:
M.Fujiki et al., Integrated Periodicals, 26, (3-4) 269-275 (1999).
J.S. Casas et al., Jpn. J. Appl. Phys., 38, L446-L450 (1999).
4. I have read and am familiar with the above-identified patent application as well as the Official Action dated **Aug. 28, 2007**, in this application.
5. I have read and am familiar with the contents of cited references, U.S. Patent Nos. **6,300,654** to **Crommance et al.**; **6,444,099** to **Sanki et al.**; and **6,564,873** to **Matsuura et al.** cited in the above-identified application.